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Vishay Semiconductors

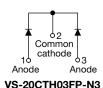
RoHS

HALOGEN FREE

# Hyperfast Rectifier, 2 x 10 A FRED Pt®



TO-220 FullPAK 3L



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	2 x 10 A			
V <sub>R</sub>	300 V			
V <sub>F</sub> at I <sub>F</sub>	0.85 V			
t <sub>rr</sub> typ.	See Recovery table			
T <sub>J</sub> max.	175 °C			
Package	TO-220 FullPAK 3L			
Circuit configuration	Common cathode			

#### **FEATURES**

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	$V_{RRM}$		300	V		
Average restified forward surrent per diode		T <sub>C</sub> = 135 °C	10			
Average rectified forward current per device	I <sub>F(AV)</sub>		20	Α		
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	120			
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	I <sub>R</sub> = 100 μA	300	-	-	.,
Forward voltage V <sub>F</sub>		I <sub>F</sub> = 10 A	=	1.05	1.25	V
	I <sub>F</sub> = 10 A, T <sub>J</sub> = 125 °C	-	0.85	0.95		
Reverse leakage current I <sub>R</sub>		$V_R = V_R$ rated	-	-	20	
		$T_J = 125  ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	6	200	μA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 300 V	-	30	=	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body		8	-	nH



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	35	
Payarea racayary timo	Reverse recovery time t <sub>rr</sub>	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	30	
neverse recovery time		T <sub>J</sub> = 25 °C		-	31	-	ns A
		T <sub>J</sub> = 125 °C		-	42	-	
Peak recovery current I <sub>RRM</sub>	ı	T <sub>J</sub> = 25 °C	$I_F = 10 \text{ A}$	-	2.4	-	
	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	5.6	-		
Reverse recovery charge Q <sub>rr</sub>	0	T <sub>J</sub> = 25 °C	•	-	36	ı	nC
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	120	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction-to-case per diode	R <sub>thJC</sub>	Mounting surface, flat, smooth, and greased	-	-	3.9	°C/W
Marking device		Case style TO-220 FullPAK 3L	20CTH03FP			

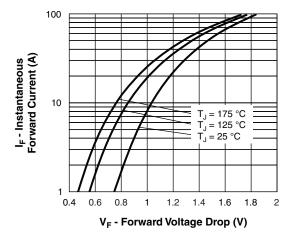


Fig. 1 - Typical Forward Voltage Drop Characteristics

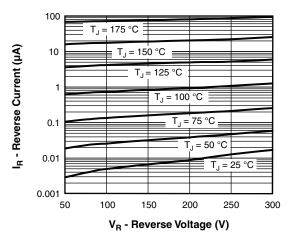


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

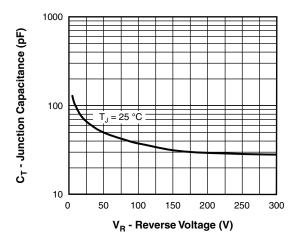


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



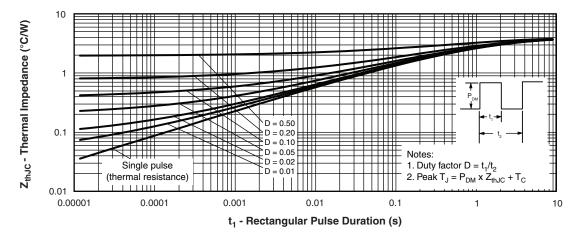


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

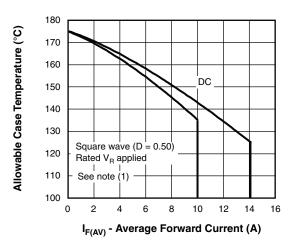


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

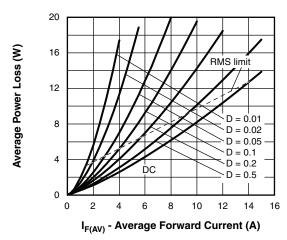


Fig. 6 - Forward Power Loss Characteristics

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5);} \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 

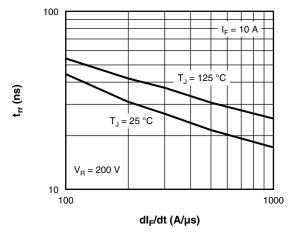


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

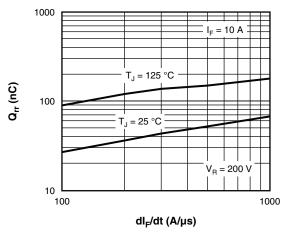
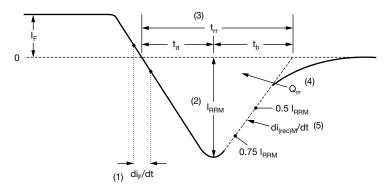


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

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- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RBM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RBM}$

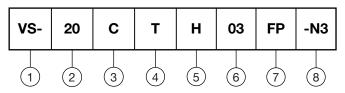
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

Current rating (20 = 20 A)

3 - C = common cathode

T = TO-220, D<sup>2</sup>PAK (TO-263AB)

5 - H = hyperfast recovery

6 - Voltage rating (03 = 300 V)

7 - FP = TO-220 FullPAK 3L

8 - Environmental digit:

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFO	RMATION (Example)		
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-20CTH03FP-N3	50	1000	Antistatic plastic tube

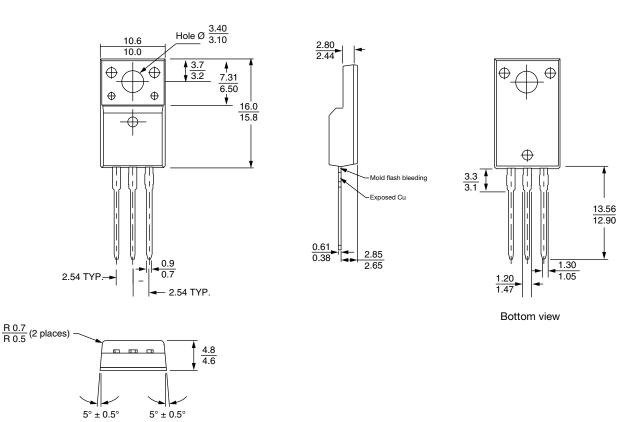
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96155
Part marking information	www.vishay.com/doc?95456
SPICE model	www.vishay.com/doc?96584



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### **3L TO-220 FullPAK**

#### **DIMENSIONS** in millimeters



#### **Notes**

- (1) All dimensions are in mm
- (2) Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils



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